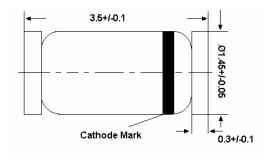
LL103A...LL103C

SILICON SCHOTTKY BARRIER DIODES

for general purpose applications

The LL103A, B, C is a metal on Silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other uses are for click suppression, efficient full wave bridges in telephone subsets, and as blocking diodes in rechargeable low voltage battery systems.

This diode is also available in DO-35 case with type designation SD103A, B, C.



Glass case MiniMELF Dimensions in mm

Absolute Maximum Ratings $(T_a = 25^{\circ}C)$

		Symbol	Value	Unit
Peak Reverse Voltage	LL103A	V_{RRM}	40	V
	LL103B	V_{RRM}	30	V
	LL103C	V_{RRM}	20	V
Power Dissipation (Infinite Heatsink)				
Tc = 3/8 from body		P _{tot}	400 ¹⁾	mW
Derates at 4 mW/°C to 0 at 125 °C				
Single Cycle Surge 60Hz sinewave		I _{FSM}	15	А
Junction Temperature		Tj	125	оС
Storage Temperature Range		Ts	-55 to +175	οС
1) Valid provided that electrodes are kept at a	mbient temperature			









LL103A...LL103C

Characteristics at T_{amb} = 25°C

		Symbol	Min.	Тур.	Max.	Unit
Forward Voltage						
at I _F = 20mA		V_{F}	-	-	0.37	V
at I _F = 200mA		V_{F}	-	-	0.6	V
Leakage Current						
at V _R = 30V	LL103A	I_R	-	-	5	uA
at $V_R = 20V$	LL103B	I_R	-	-	5	uA
at V _R =10V	LL103C	I_R	-	-	5	uA
Junction Capacitance		(50		, r
at $V_R = 0V$, $f = 1MHz$		C_{tot}	_	50	-	pF
Reverse Recovery Time		+	-	10	-	ns
at $I_F = I_R = 5$ mA to 200 mA , recover to	0.1 I _R	t _{rr}				

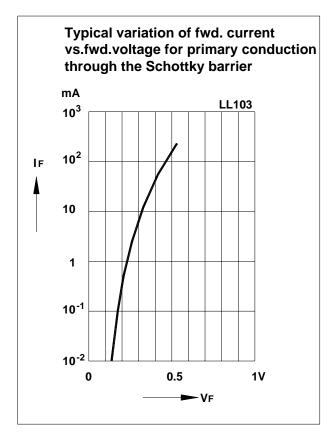


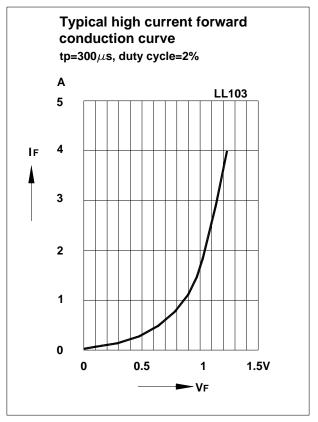


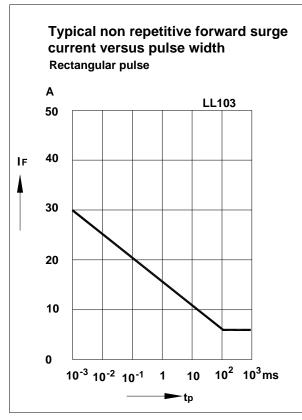


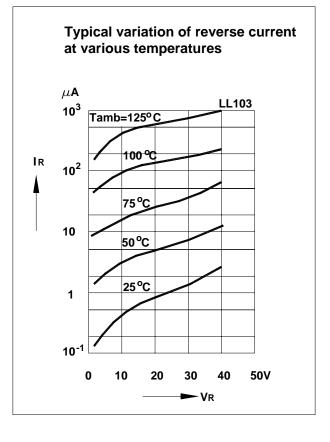


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